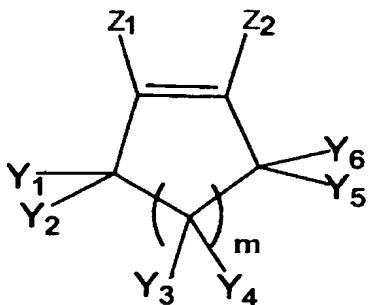


ABSTRACT OF THE DISCLOSURE

Photoresist monomers of following Formula 1, photoresist polymers thereof, and photoresist compositions containing the same. The photoresist polymers include a repeating unit comprising the photoresist monomer of Formula 1 as a comonomer and the photoresist compositions containing the same have excellent etching resistance, heat resistance and adhesiveness to a wafer, and are developable in aqueous tetramethylammonium hydroxide (TMAH) solutions. In addition, the photoresist compositions have a low light absorbance at 157nm wavelength, and thus are suitable for a photolithography process using ultraviolet light sources such as VUV (157nm) in fabricating a minute circuit for a high integration semiconductor device.

Formula 1



wherein Y_1 , Y_2 , Y_3 , Y_4 , Y_5 , Y_6 , Z_1 , Z_2 and m are defined in the specification.